# Silicon Carbide Schottky Diode

650 V, 8 A

# **Description**

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 49 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

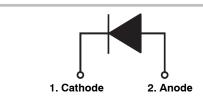
## **Applications**

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



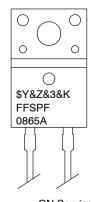
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#### **MARKING DIAGRAM**



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Data Code (Year & Week) &K = Lot

FFSPF0865A = Specific Device Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet

# **ABSOLUTE MAXIMUM RATINGS** ( $T_C = 25^{\circ}C$ , Unless otherwise noted)

Symbol	Parameter		FFSPF0865A	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage		650	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		49	mJ
I <sub>F</sub>	Continuous Rectified Forward Current @ T <sub>C</sub> < 124 °C		8	Α
	Continuous Rectified Forward Current @ T <sub>C</sub> <	135 °C	6.8	
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25 °C, 10 μs	670	Α
		T <sub>C</sub> = 150 °C, 10 μs	640	Α
I <sub>F, SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	49	Α
I <sub>F, RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	25	Α
P <sub>tot</sub>	Power Dissipation	T <sub>C</sub> = 25 °C	39	W
		T <sub>C</sub> = 150 °C	6.4	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature F	Range	-55 to + 175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ hetaJC}$	Thermal Resistance, Junction to Case, Max.	4.0	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 8 A, T <sub>C</sub> = 25°C	-	1.50	1.75	V
		I <sub>F</sub> = 8 A, T <sub>C</sub> = 125°C	-	1.6	2.0	
		I <sub>F</sub> = 8 A, T <sub>C</sub> = 175°C	-	1.72	2.4	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 650 V, T <sub>C</sub> = 25°C	-	-	200	μΑ
		V <sub>R</sub> = 650 V, T <sub>C</sub> = 125°C	-	-	400	
		V <sub>R</sub> = 650 V, T <sub>C</sub> = 175°C	-	-	600	
Q <sub>C</sub>	Total Capacitive Charge	V = 400 V	-	27	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	463	-	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	-	48	-	
		V <sub>R</sub> = 400 V, f = 100 kHz	-	38	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. E<sub>AS</sub> of 49 mJ is based on starting TJ = 25 °C, L = 0.5 mH, I<sub>AS</sub> = 14 A, V = 50 V.

# ORDERING INFORMATION

Device	Marking	Package	Packing Method	Quantity
FFSPF0865A	FFSPF0865A	TO-220F-2L	Tube	50 units

# **TYPICAL CHARACTERISTICS**

(T<sub>J</sub> = 25°C unless otherwise noted)

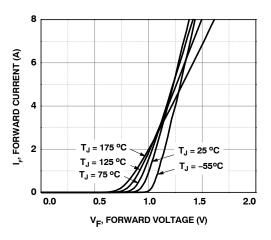


Figure 1. Forward Characteristics

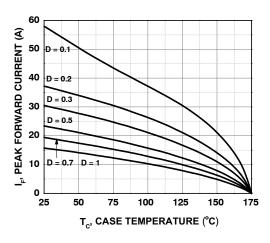


Figure 3. Current Derating

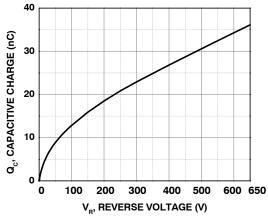


Figure 5. Capacitive Charge vs. Reverse Voltage

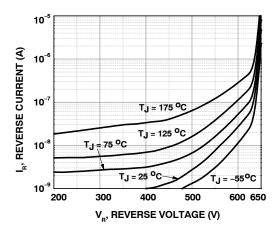


Figure 2. Reverse Characteristics

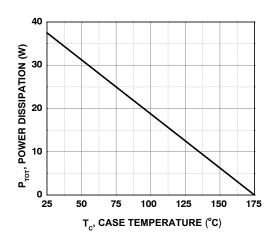


Figure 4. Power Derating

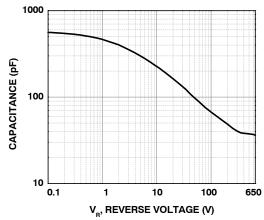


Figure 6. Capacitance vs. Reverse Voltage

#### **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$ 

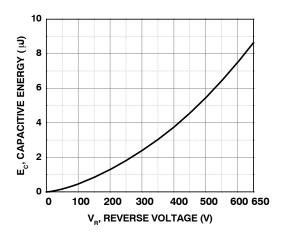


Figure 7. Capacitance Stored Energy

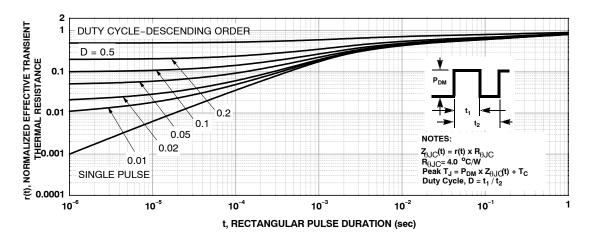


Figure 8. Junction-to-Case Transient Thermal Response Curve

# **TEST CIRCUIT AND WAVEFORMS**

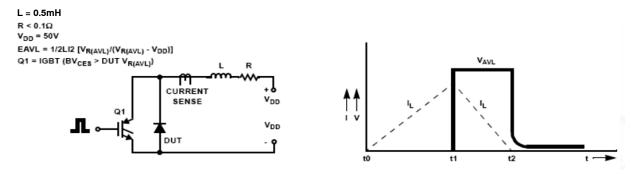
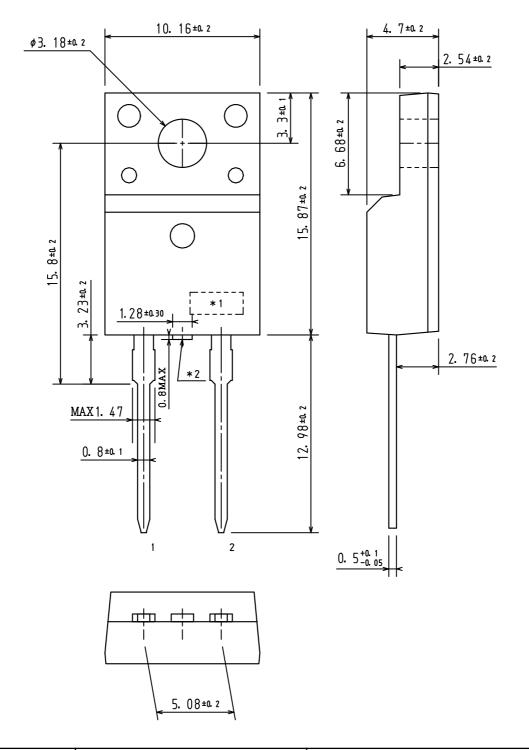


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

# TO-220 Fullpack, 2-Lead / TO-220F-2FS CASE 221AS ISSUE O

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